

a driving circuit including a second plurality of thin film transistors formed over the insulating surface of the first substrate for driving said active matrix circuit;

a second substrate facing said first substrate with a liquid crystal material interposed therebetween, said first substrate having an extended portion which extends beyond at least one side edge of the second substrate wherein said second substrate covers said active matrix circuit and said driving circuit; and

*Cont'd*  
*m1* at least one semiconductor integrated circuit chip disposed over the extended portion of the first substrate and operationally connected to said driving circuit wherein said integrated circuit chip is at least one of a memory, an input port, a correction memory and a CPU,

wherein said first and second plurality of thin film transistors are formed from a common semiconductor film formed over said first substrate, and each of said first plurality of thin film transistors has at least one lightly doped drain between a channel region and a drain region thereof.

---

36. (Amended) A display device comprising:

a first substrate having an insulating surface;

an active matrix circuit including a first plurality of thin film transistors formed on the insulating surface of the first substrate;

a driving circuit including a second plurality of thin film transistors formed over the insulating surface of the first substrate for driving said active matrix circuit;

*m2* a second substrate facing said first substrate with a gap therebetween, said first substrate having an extended portion which extends beyond at least one side edge of the second substrate wherein said second substrate covers said active matrix circuit and said driving circuit; and

at least one semiconductor integrated circuit chip disposed over the extended portion of the first substrate and operationally connected to said driving circuit,

*contd*  
*M2* wherein each of said first plurality of thin film transistors is a bottom gate type transistor in which a gate electrode is located below a channel region of the transistor, and each of said second plurality of thin film transistors is a top gate type transistor in which a gate electrode is located over a channel region of the transistor.

---

*M3* 38. (Amended) A display device comprising:  
a first substrate having an insulating surface;  
an active matrix circuit including a first plurality of thin film transistors formed on the insulating surface of the first substrate;  
a driving circuit including a second plurality of thin film transistors formed over the insulating surface of the first substrate for driving said active matrix circuit; and  
a second substrate facing said first substrate with a gap therebetween, said first substrate having an extended portion which extends beyond at least one side edge of the second substrate;  
at least one semiconductor integrated circuit chip disposed over the extended portion of the first substrate and operationally connected to said driving circuit, wherein said semiconductor integrated circuit chip is selected from the group consisting of a correction memory, a memory, a CPU, and an input port.

---

*contd*  
*M4* 51. (Amended) An electric device comprising:  
an insulating substrate;  
an active matrix circuit including at least one thin film transistor formed over a first surface of said insulating substrate;  
a driving circuit including at least another one thin film transistor for driving the active matrix circuit formed over said first surface of the insulating substrate; and  
at least one semiconductor integrated circuit chip disposed over said first surface of the extended portion of the insulating substrate and operationally connected